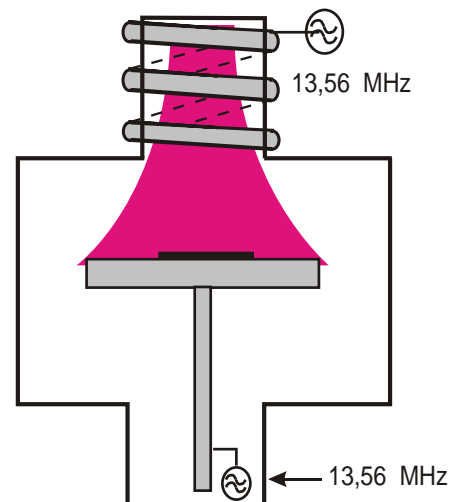
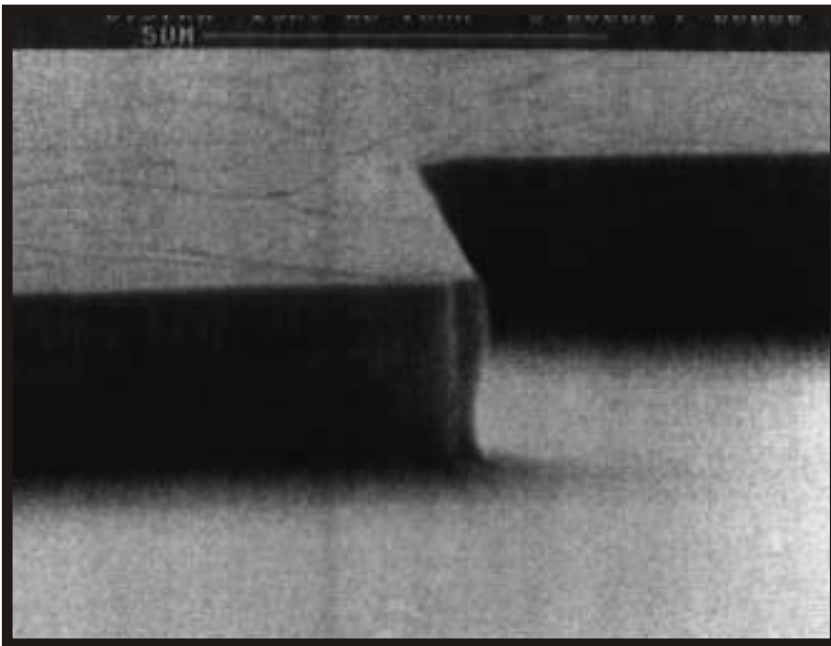


# Plasmalab Data

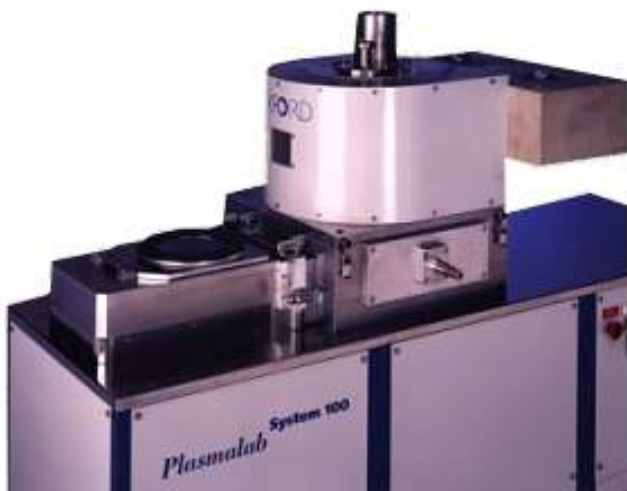
## Low Damage ICP-RIE: InGaAs / GaAs



3 µm deep etch through InGaAs / GaAs (Photoresist not removed)  
Courtesy of Siemens AG, ZFE, Munich

### Plasmalab 80 Plus

### Plasmalab System 133



#### Technology:

Inductive Coupled Plasma - RIE  
13 MHz induced RF bias  
Chlor based process

\*original work by ECR, see:  
[http://www.oxfordplasma.de/technols/rie\\_ecr.htm](http://www.oxfordplasma.de/technols/rie_ecr.htm)

#### Results:

Low damage etch (by two step process)  
Etch Rate : ca. 50 nm / min  
Selectivity to PR: ca. 15:1  
Uniformity: better than +/- 3 % (4" diam.)

### Plasmalab System 100